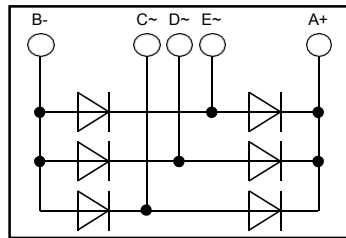


Diode Modules TG-PAK

Features

- International standard package
- With DBC ceramic base plate
- Planar passivated chips
- High surge capability
- Complies With RoHS Directive;
- Lead Free;



**IdAVM = 200A**  
**VRRM = 800-1600V**

Benefits

- Supplies for DC power equipment
- Input rectifiers for PWM inverter
- Field supply for DC motors
- Battery DC power supplies



Absolute Maximum Ratings

Symbol	Test Conditions	Max.	Units
VRRM		800,1200,1400,1600	V
IdAVM	Tc=100 °C, module	200	A
IfSM	Tvj=45 °C; t=10ms (50 Hz),1/2cycle	2000	A
	Tvj=45 °C;t=8.3ms (60 Hz),1/2cycle	2200	A
I²t	Tvj=45 °C; t=10ms (50 Hz),1/2cycle	20000	A²s
	Tvj=45 °C;t=8.3ms (60 Hz),1/2cycle	20100	
VISOL	RMS Isolation Voltage, Any Terminal To Case, t=1 min	2500	V
Tvj		-40 to +150	°C
TvjM		150	
TSTG		-40 to +125	

**Thermal / Mechanical Characteristics**

	Parameter	Typ.	Max.	Units
R <sub>θJS</sub>	Thermal Resistance, Junction-to- Sink DC	-	0.5	
R <sub>θJC</sub>	Thermal Resistance, Junction-to- Case DC	-	0.4	°C/W
R <sub>θCS</sub>	Thermal Resistance, Case-to- Sink- Module	0.1	-	
	Mouting Torque, Case-to-Heatsink	-	4.0	N.m
	Mouting Torque, Case-to-Terminal 1,2 & 3	-	3.0	N.m
	Weight of Module	250	-	g

**Electrical Characteristics (unless otherwise specified)**

	Parameter	Min.	Typ.	Max.	Units	Conditions
I <sub>R</sub>	Diode Leaking Current	-	-	0.5	mA	T <sub>VJ</sub> =25 °C V <sub>R</sub> =V <sub>RRM</sub>
		-	-	10	mA	T <sub>VJ</sub> =125 °C V <sub>R</sub> =V <sub>RRM</sub>
V <sub>F</sub>	Diode Forward Voltage	-	-	1.45	V	I <sub>F</sub> =200A; T <sub>VJ</sub> =25 °C
V <sub>TO</sub>	For power-loss calculations only	-	-	0.8	V	T <sub>VJ</sub> =125°C
r <sub>T</sub>		-	-	3.0	mΩ	

**Case Outline - MDS-pak**

